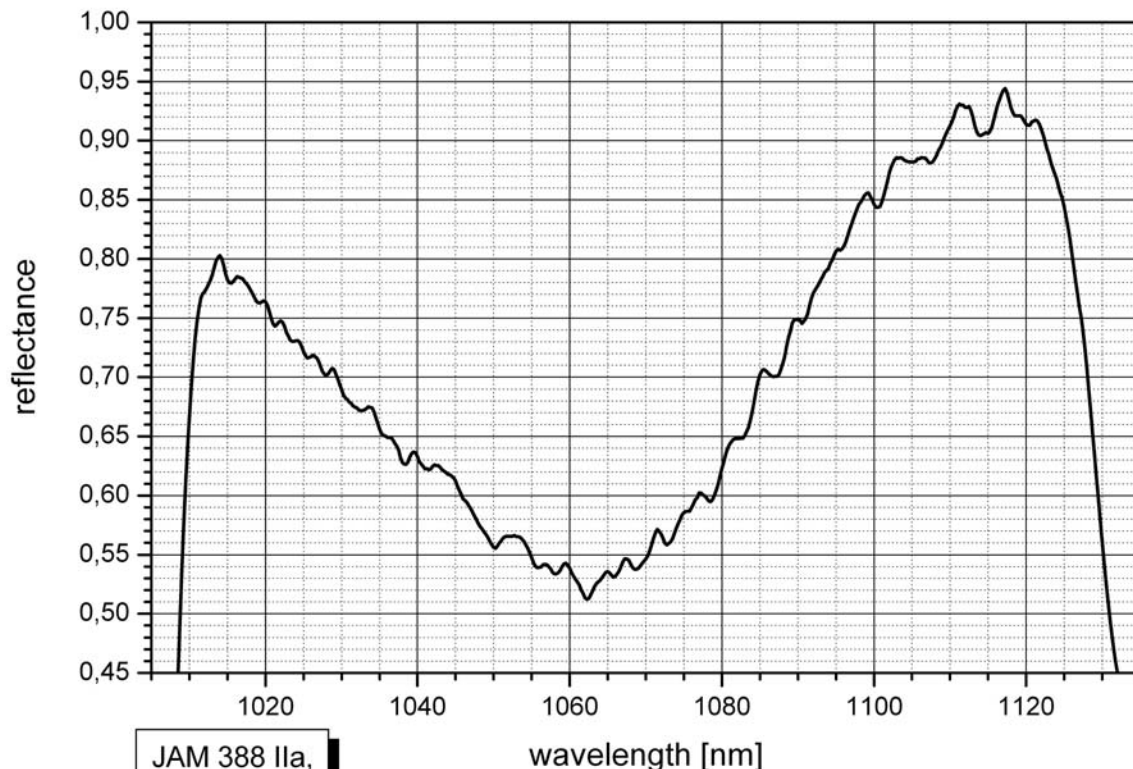


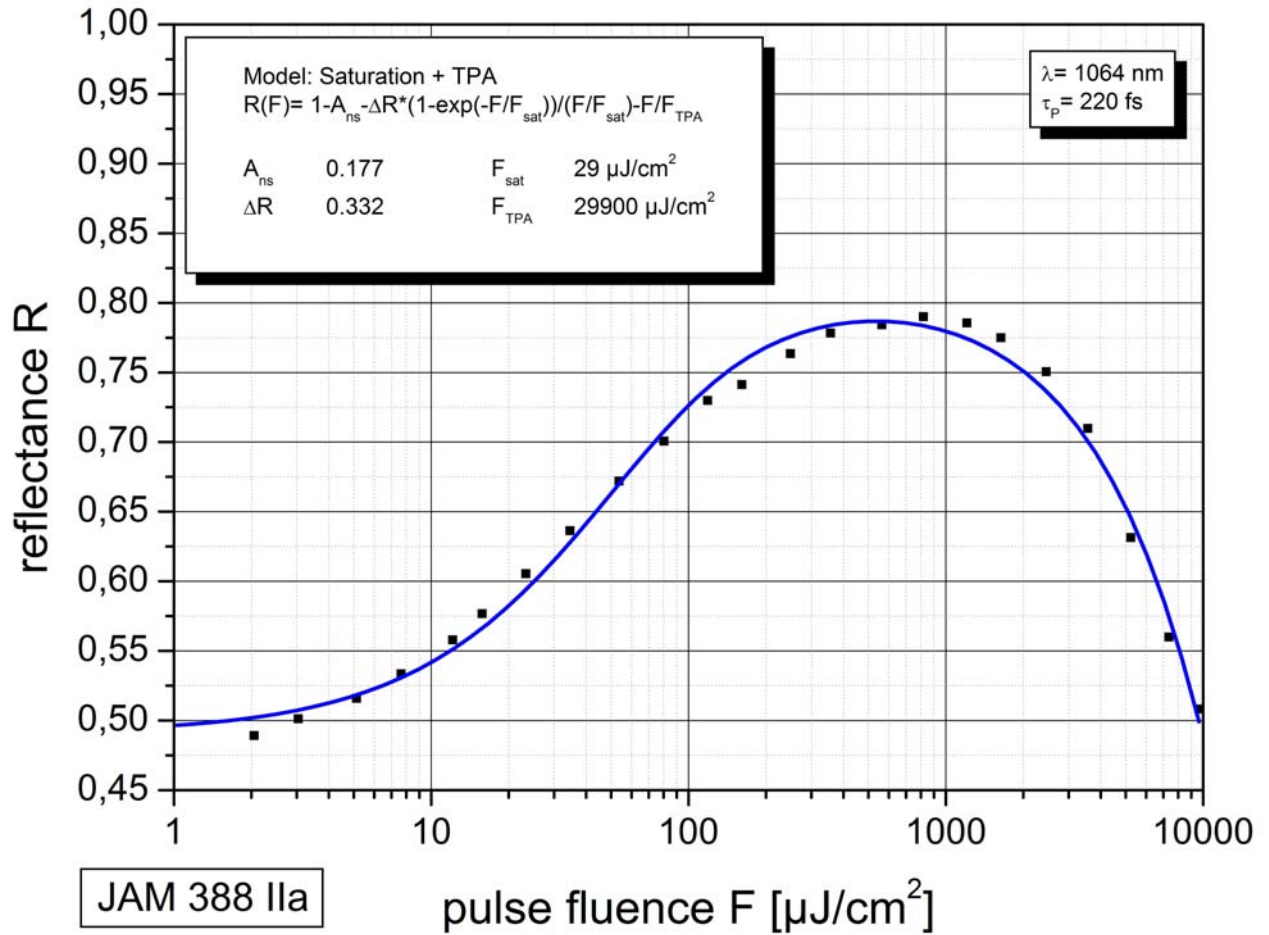
## SAM™ data sheet SAM-1064-50-x-2ps, $\lambda = 1064 \text{ nm}$

Laser wavelength	$\lambda = 1064 \text{ nm}$
High reflection band (R > 55%)	$\lambda = 1010 \dots 1120 \text{ nm}$
Absorptance	$A_0 = 50 \%$
Modulation depth	$\Delta R = 33 \%$
Non-saturable loss	$A_{ns} = 17 \%$
Saturation fluence	$\Phi_{sat} = 29 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 2 \text{ ps}$
Absorber layer	multiple quantum well
Damage threshold	200 MW/cm <sup>2</sup>
Chip area	4mm x 4mm; other dimensions on request
Chip thickness	400 $\mu\text{m}$ ; optional: 150 $\mu\text{m}$ on request
Protection	the SAM is protected with a dielectric front layer
Mounting of SAM-1064-50-x-2ps	denotes the type of mounting as follows:
<b>x</b> = 0	unmounted
<b>x</b> = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm $\varnothing$
<b>x</b> = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm $\varnothing$
<b>x</b> = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $\varnothing$
<b>x</b> = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm $\varnothing$
<b>x</b> = FC/PC	mounted on a 1 m monomode fiber cable with FC/PC connector

### Low intensity spectral reflectance



## Saturation measurement



## Pump-probe measurement of SAM-1064-70-x-2ps from the same wafer

